OIPE JC105 FEB 13 2004 PATENT & TRADEMARK OFFICE

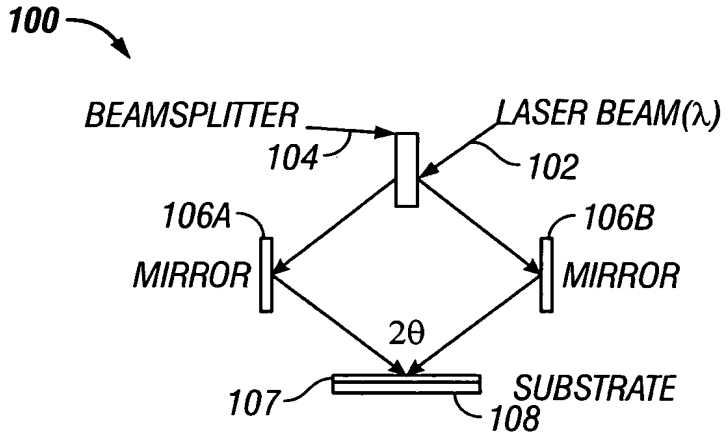

FIG. 1A

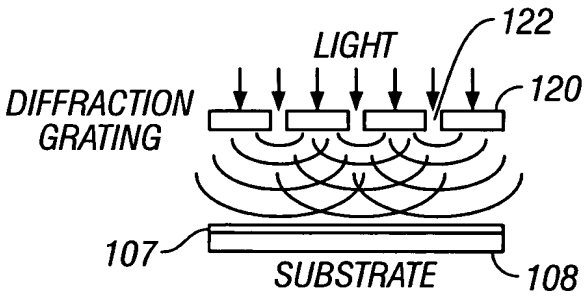

FIG. 1B

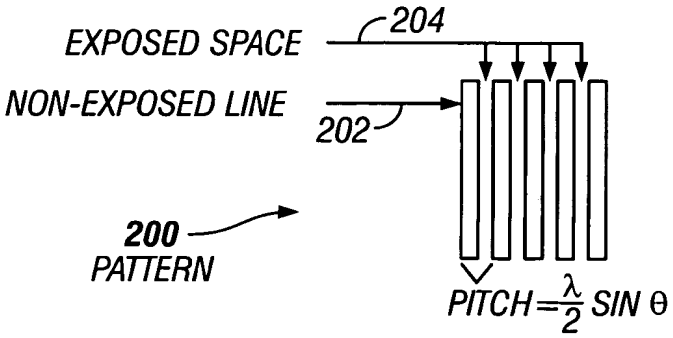

FIG. 2

OIPE JC105 FEB 13 2004 PATENT & TRADEMARK OFFICE

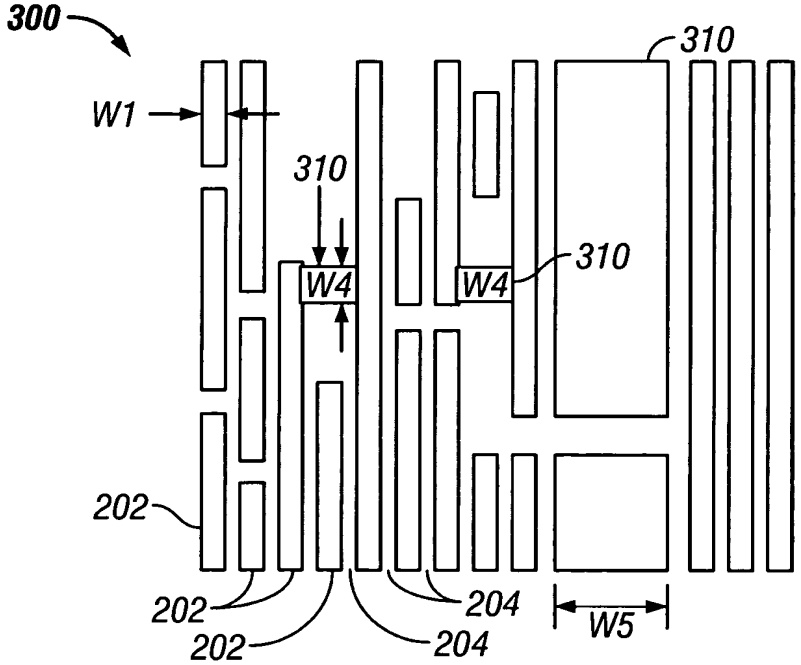

FIG. 3A

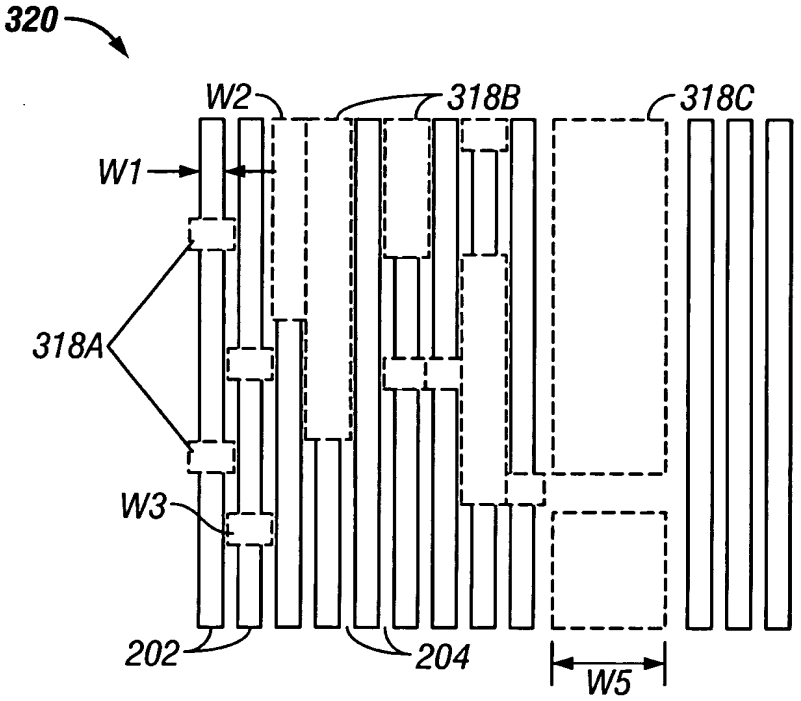

FIG. 3B

OIPE
FEB 1 3 2004
PATENT & TRADEMARK OFFICE
JC105

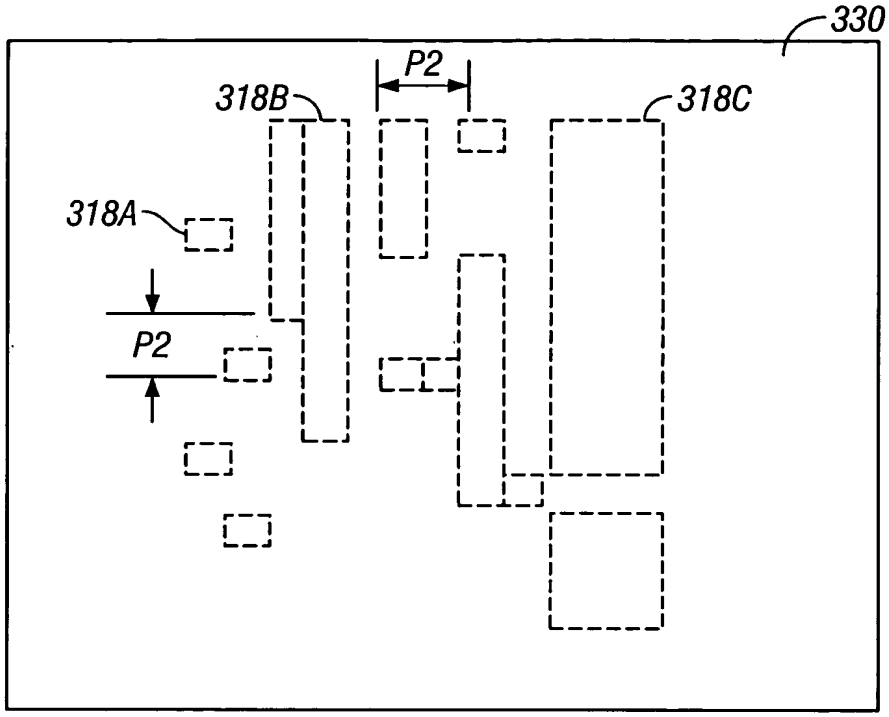

FIG. 3C

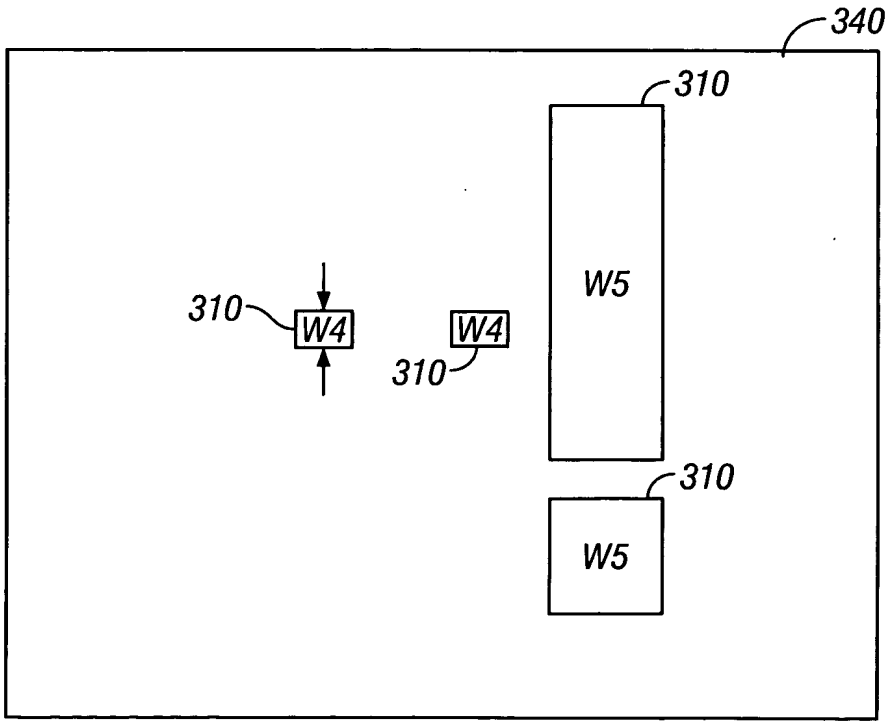

FIG. 3D

OIPE FEB 13 2004 PATENT & TRADEMARK OFFICE JC105

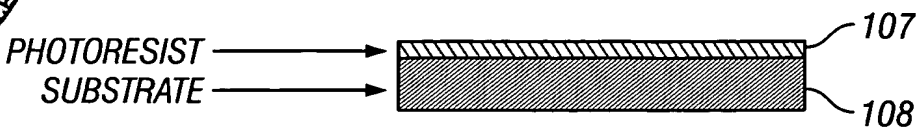

FIG. 4A

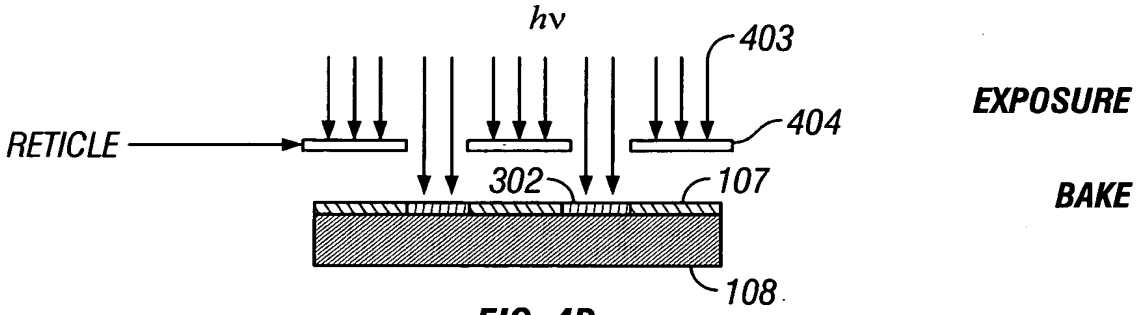

FIG. 4B

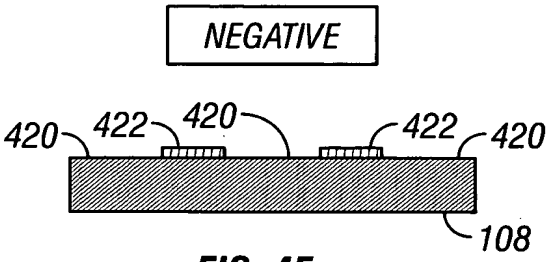

FIG. 4F

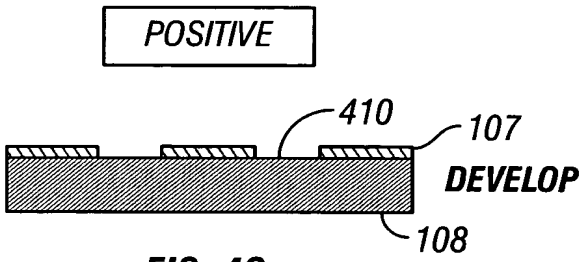

FIG. 4C

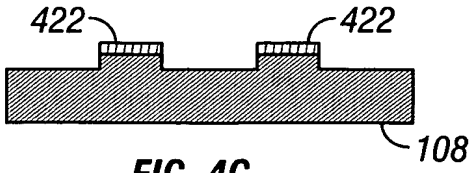

FIG. 4G

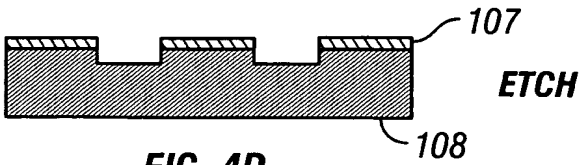

FIG. 4D

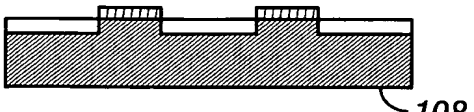

FIG. 4H

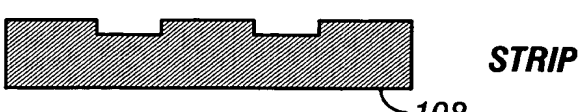

FIG. 4E

OIPE FEB 13 2004 JC105 PATENT & TRADEMARK OFFICE

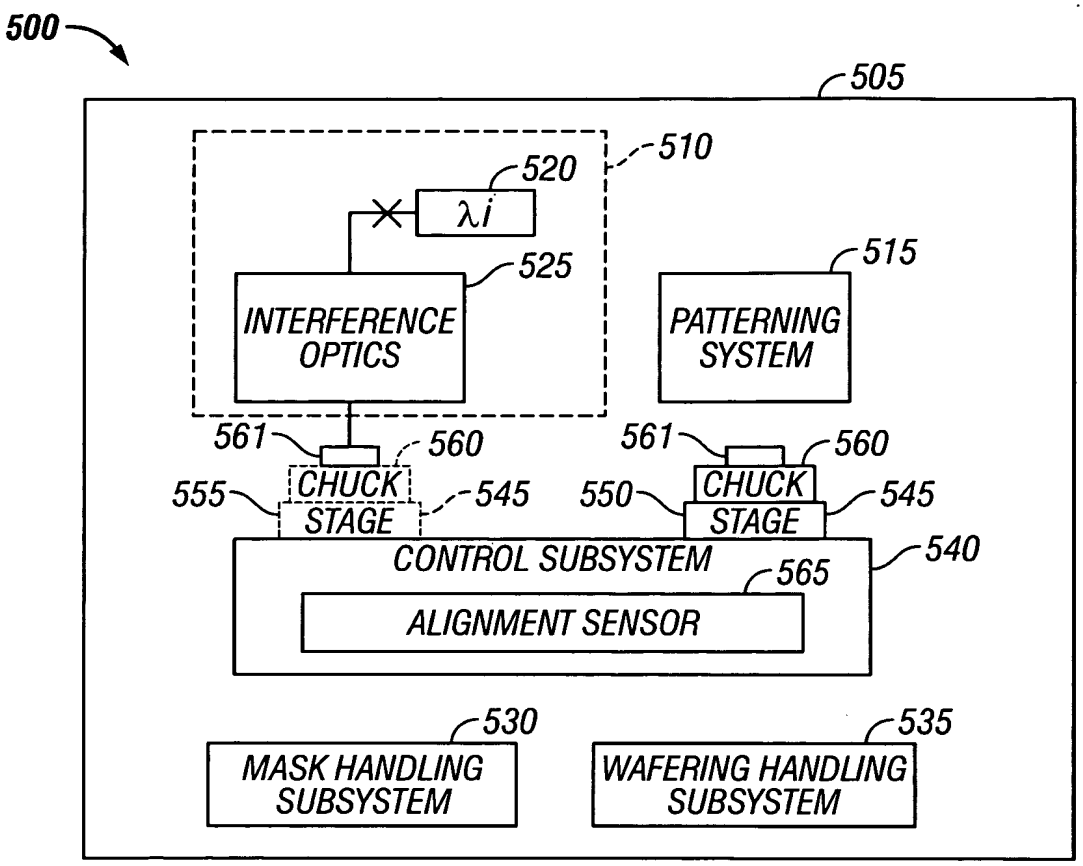

FIG. 5

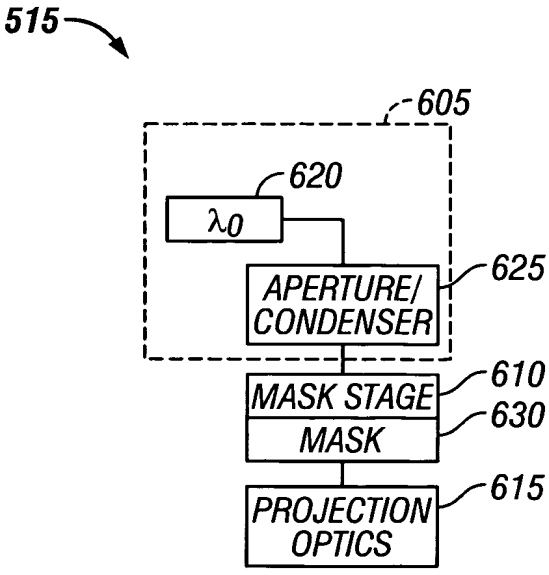

FIG. 6

OIPE
FEB 13 2004
PATENT & TRADEMARK OFFICE
JC105

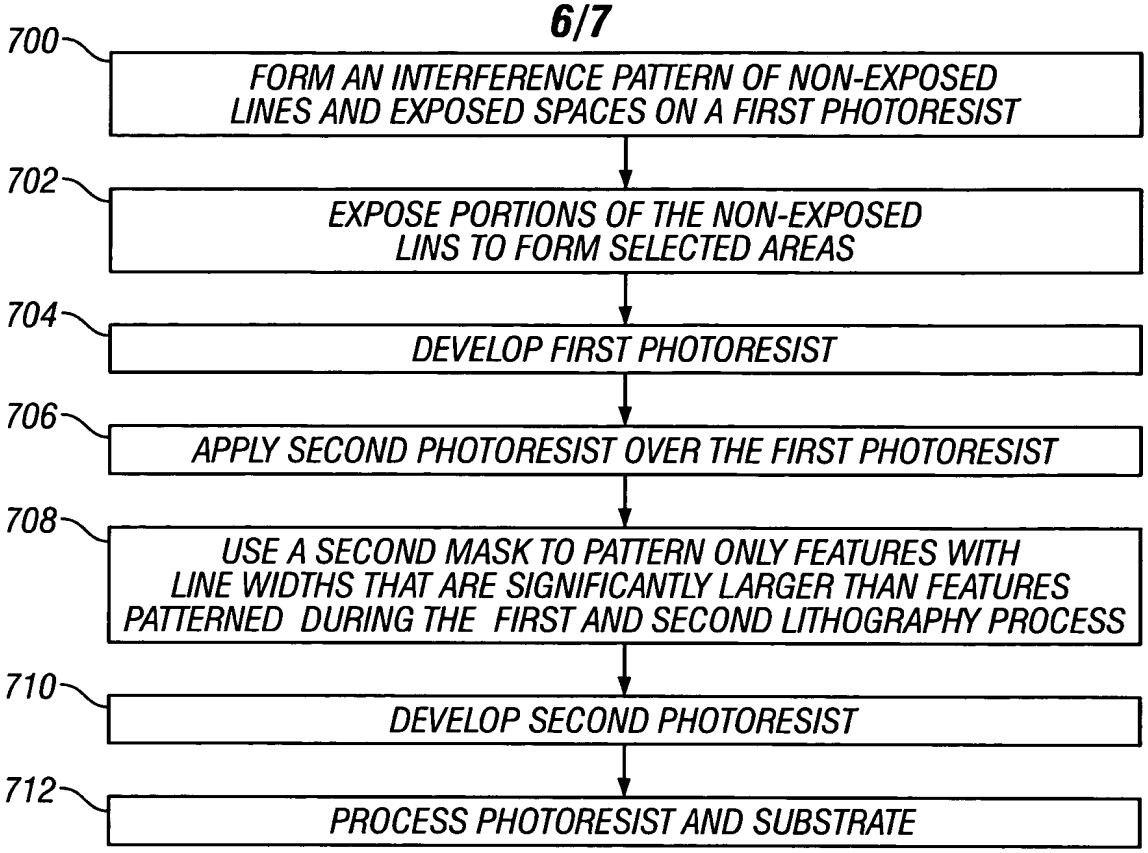
700
FORM AN INTERFERENCE PATTERN OF NON-EXPOSED LINES AND EXPOSED SPACES ON A FIRST PHOTORESIST
702
EXPOSE PORTIONS OF THE NON-EXPOSED LINS TO FORM SELECTED AREAS
704
DEVELOP FIRST PHOTORESIST
706
APPLY SECOND PHOTORESIST OVER THE FIRST PHOTORESIST
708
USE A SECOND MASK TO PATTERN ONLY FEATURES WITH LINE WIDTHS THAT ARE SIGNIFICANTLY LARGER THAN FEATURES PATTERNED DURING THE FIRST AND SECOND LITHOGRAPHY PROCESS
710
DEVELOP SECOND PHOTORESIST
712
PROCESS PHOTORESIST AND SUBSTRATE

FIG. 7

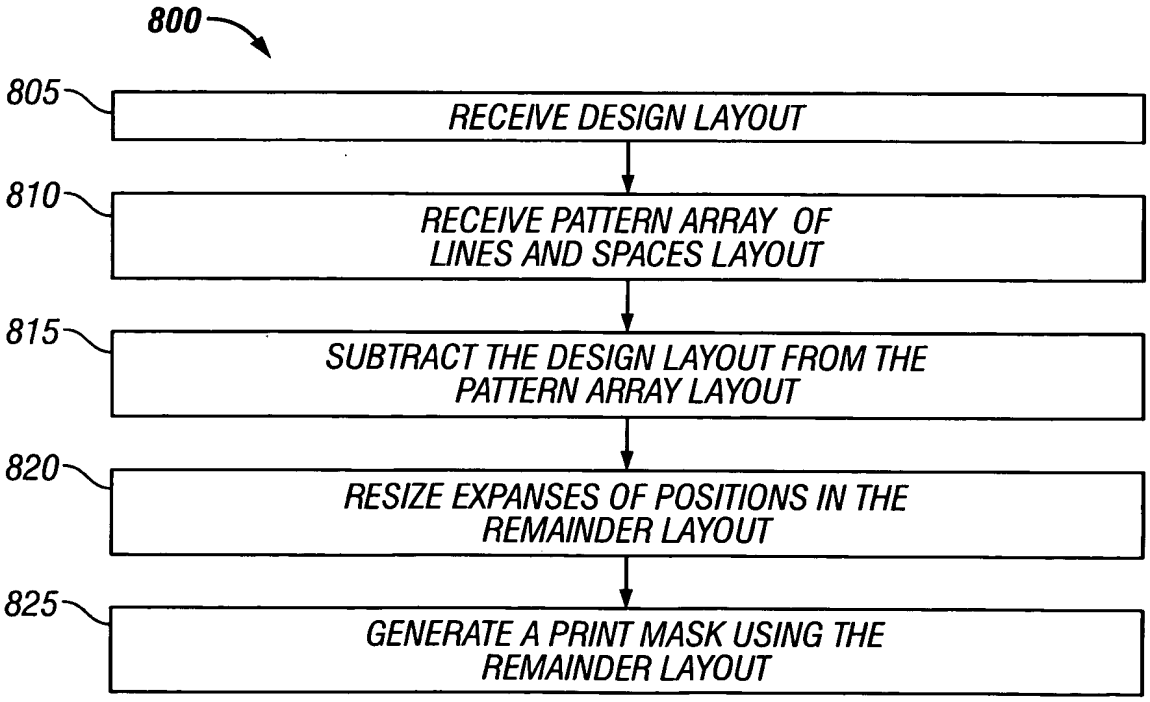

FIG. 8

OIPE
FEB 13 2004
PATENT & TRADEMARK OFFICE
JC103

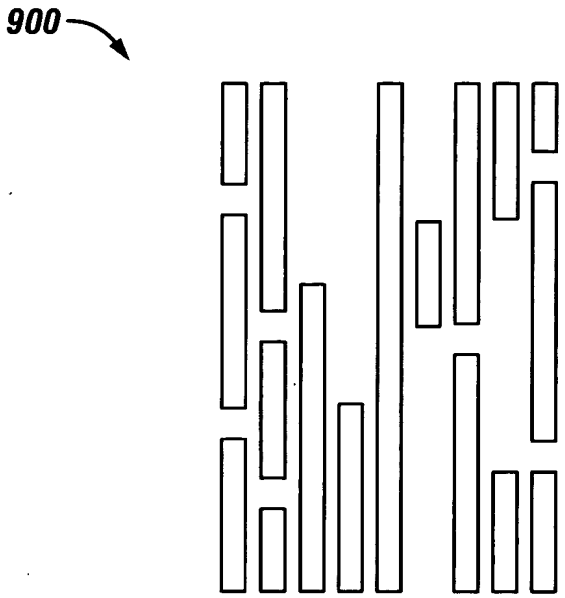

FIG. 9

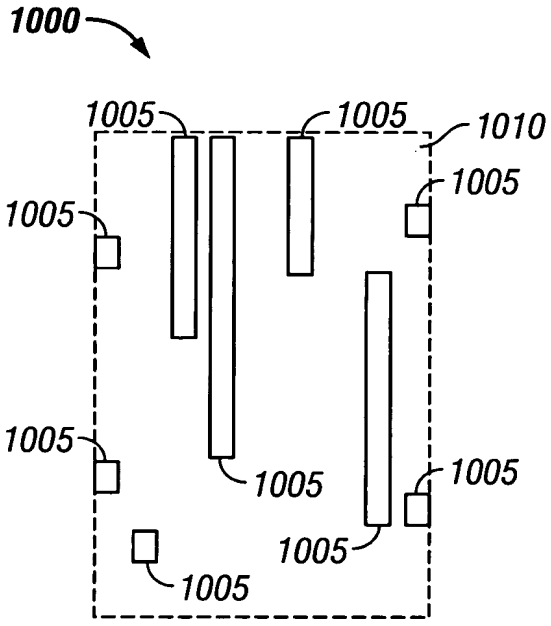

FIG. 10

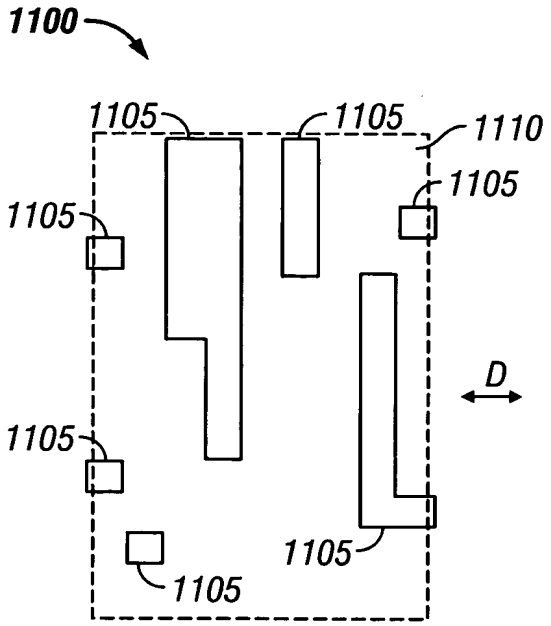

FIG. 11